



# MMBD2838<sup>\*</sup>

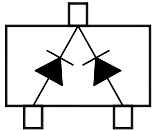
## Silicon Epitaxial Planar Switching Diode

### Features

- Small package
- Low forward voltage
- Fast reverse recovery time

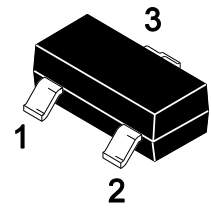
### Pin Configuration

3.Cathode1、Cathode2



1.Anode1 2.Anode2

### Package



1.Anode1 2.Anode2  
3.Cathode1、Cathode2

Marking Code : A61

### Electrical Characteristics (at $T_J = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	$V_{RRM}$	85	V
Reverse Voltage	$V_R$	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	$I_{FM}$	300	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	1	A
Maximum Power Dissipation	$P_D$	150	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 to +150	$^\circ\text{C}$

### Electrical Characteristics (at $T_J = 25^\circ\text{C}$ )

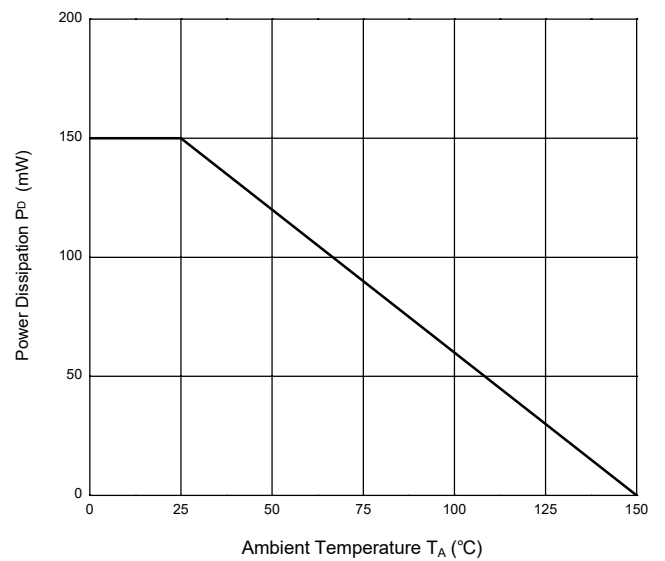
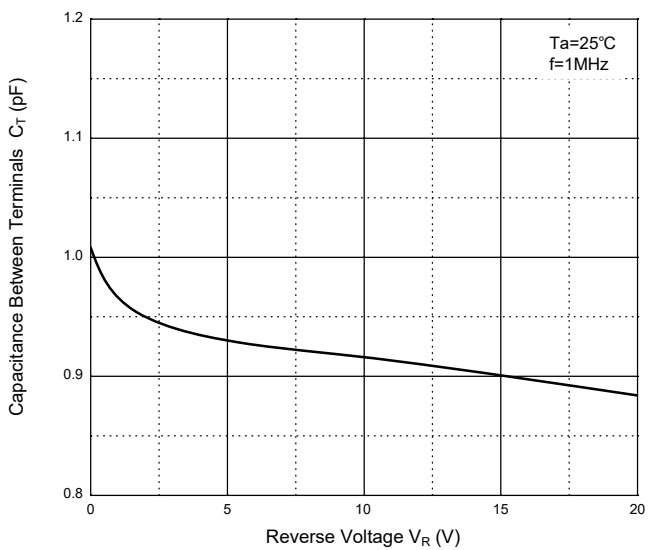
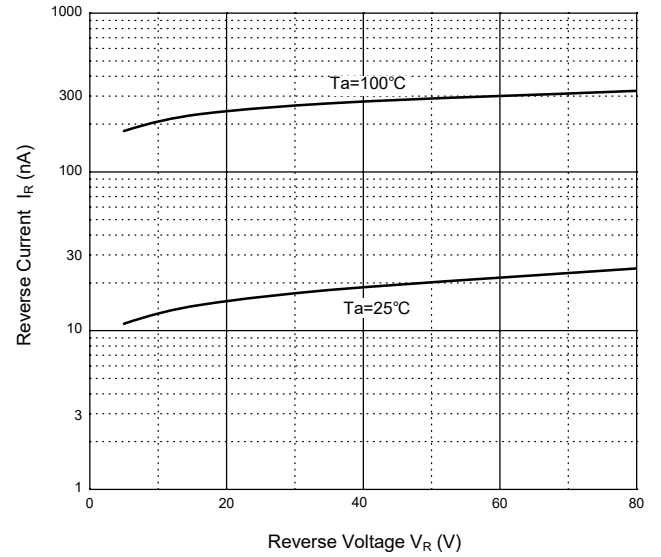
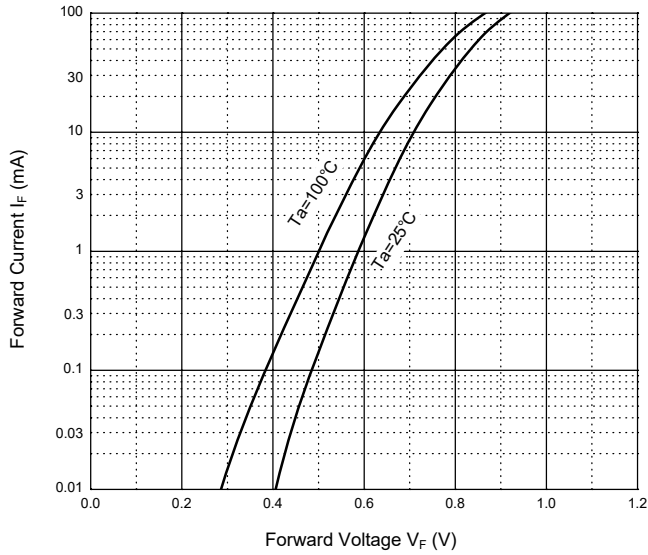
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$	$V_F$	0.6 0.7 0.9	-- -- 1.2	V
Reverse Current at $V_R = 70\text{ V}$	$I_R$	--	1	$\mu\text{A}$
Typical Junction Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_j$	--	4	pF
Maximum Reverse Recovery Time at $I_F = 10\text{ mA}$ , $V_R = 6\text{ V}$ , $I_{RR} = 0.1 \times I_R$ , $R_L = 100\Omega$	$T_{rr}$	--	4	nS



# MMBD2838<sup>†</sup>

## Silicon Epitaxial Planar Switching Diode

### Typical Characteristic Curves





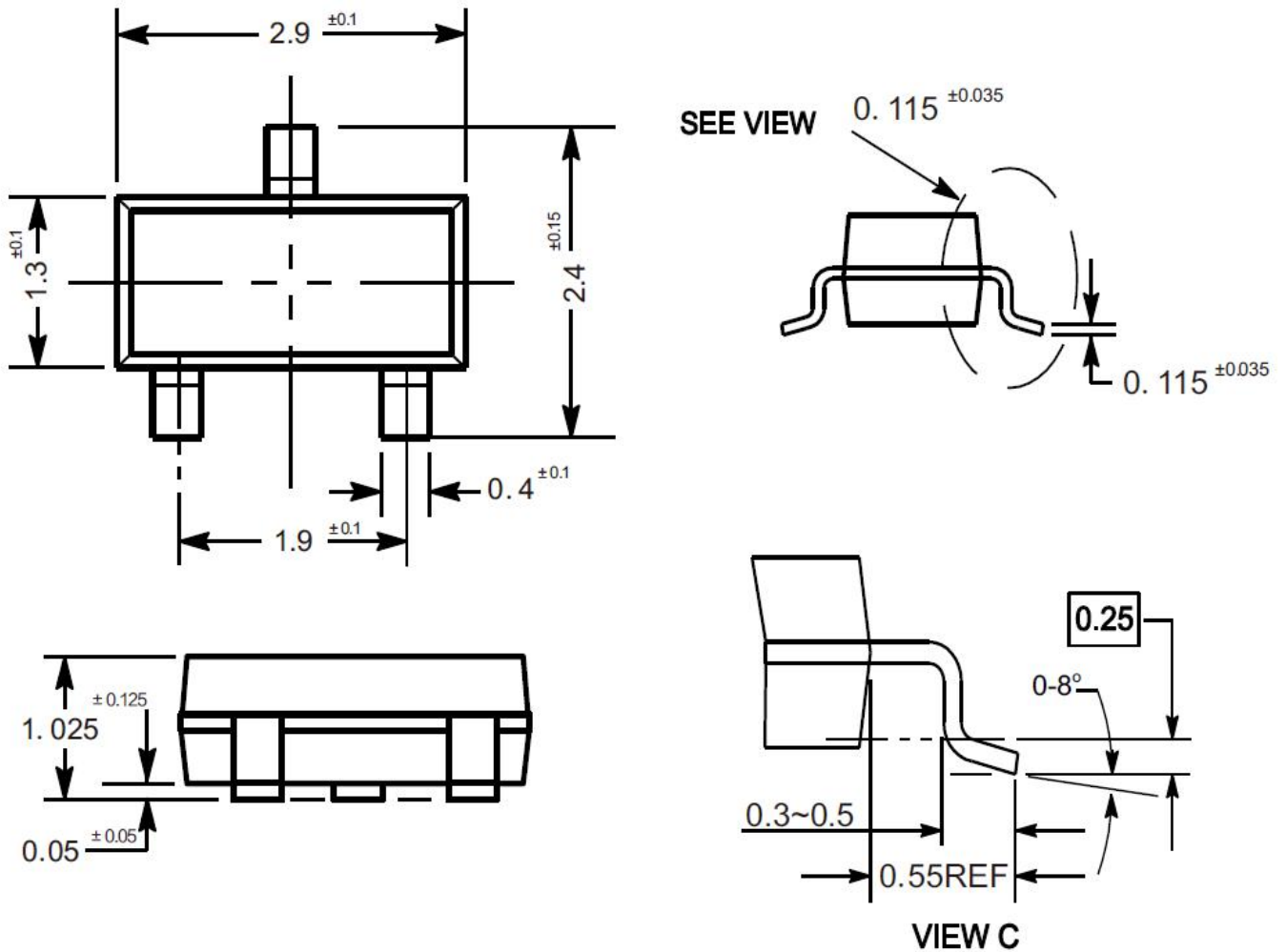
# MMBD2838<sup>†</sup>

## Silicon Epitaxial Planar Switching Diode

### Package Outline

SOT-23

Dimensions in mm



### Ordering Information

Device	Package	Shipping
MMBD2838	SOT-23	3,000PCS/Reel&7inches